PSMN4R1-30YLC

N-channel 30 V 4.35mΩ logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 27 September 2011 Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching
- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

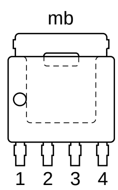
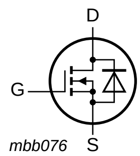
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C	-	-	30	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1	-	-	92	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2	-	-	67	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 20 A; T_j = 25 °C; see Figure 12	-	4.75	5.7	mΩ
		V_{GS} = 10 V; I_D = 20 A; T_j = 25 °C; see Figure 12	-	3.65	4.35	mΩ

Table 1. Quick reference data *...continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 20 A; V_{DS} = 15 V; see Figure 14; see Figure 15	-	3.5	-	nC
$Q_{G(tot)}$	total gate charge	V_{GS} = 4.5 V; I_D = 20 A; V_{DS} = 15 V; see Figure 14; see Figure 15	-	11	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R1-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
PSMN4R1-30YLC	4C130L

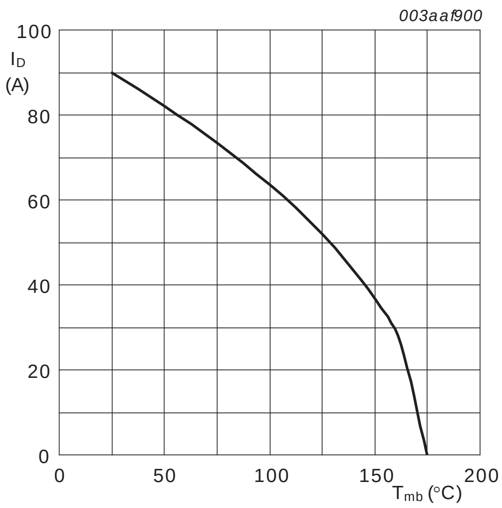
[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

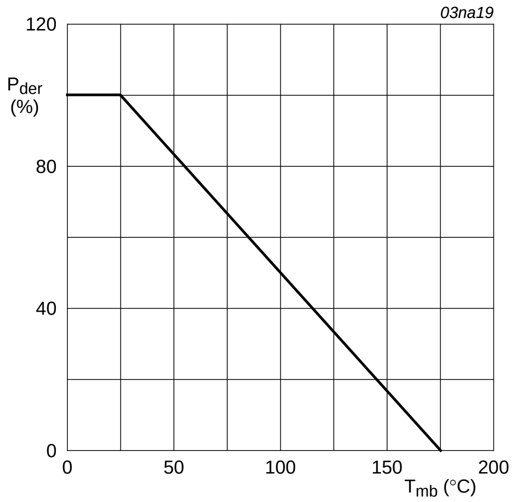
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C	-	30	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see Figure 1	-	92	A
		V_{GS} = 10 V; T_{mb} = 100 °C; see Figure 1	-	65	A
I_{DM}	peak drain current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C; see Figure 4	-	367	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2	-	67	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	270	-	V
Source-drain diode					
I_S	source current	T_{mb} = 25 °C	-	61	A
I_{SM}	peak source current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C	-	367	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 92 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω; unclamped; see Figure 3	-	21	mJ



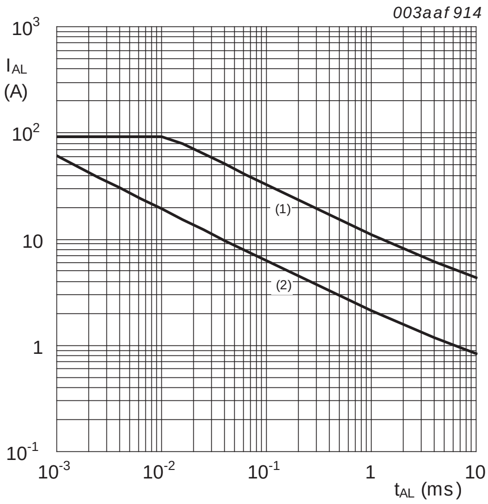
$$V_{GS} \geq 10V$$

Fig 1. Continuous drain current as a function of mounting base temperature



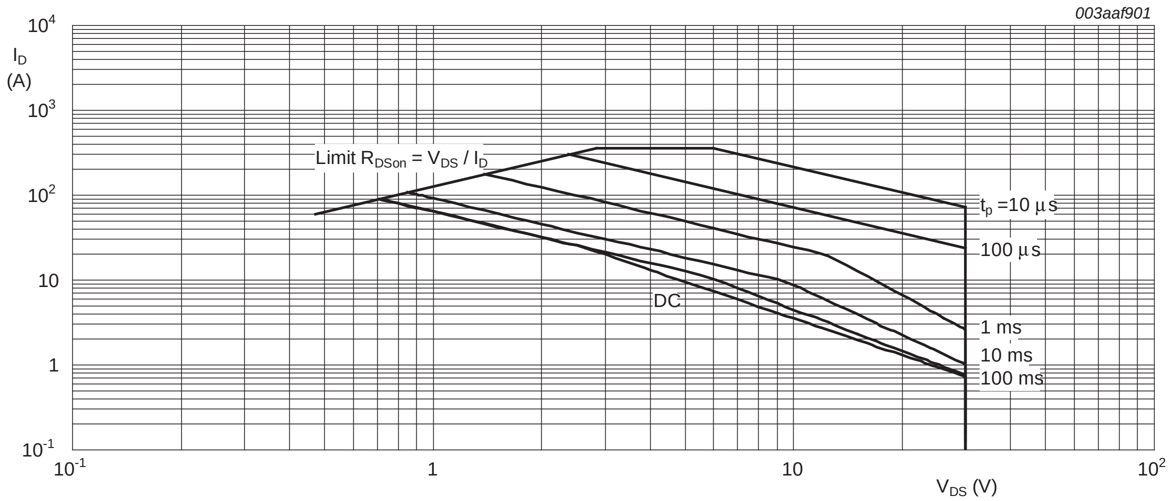
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 100°C$

Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



$T_{mb} = 25°C$; I_{DM} is a single pulse

Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	2.05	2.24	K/W

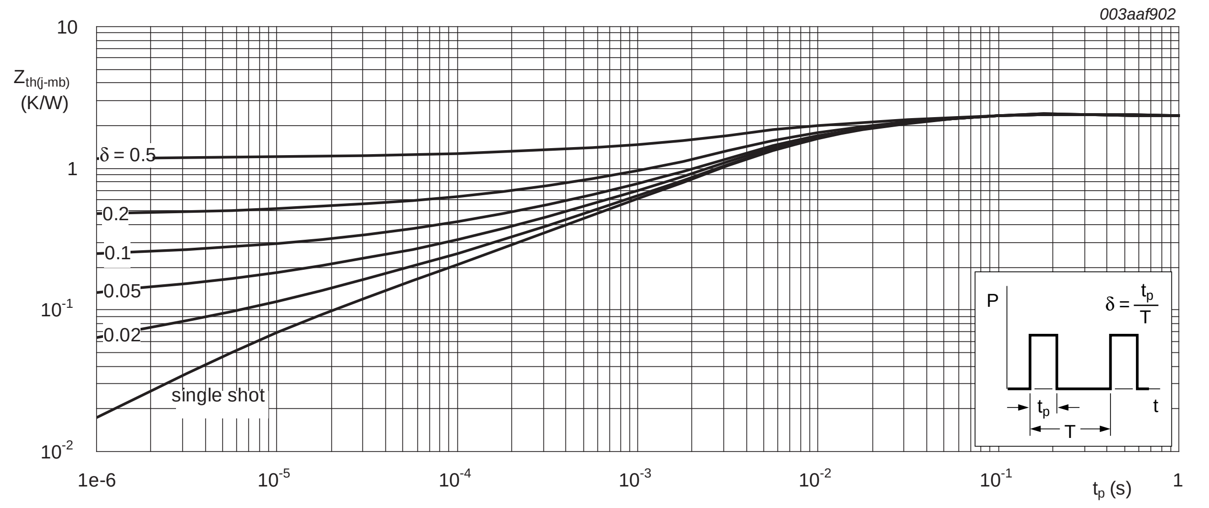


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

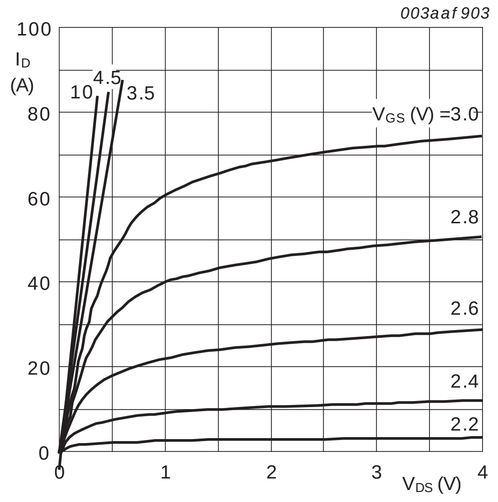
7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 10; see Figure 11	1.05	1.58	1.95	V
		I_D = 10 mA; V_{DS} = V_{GS}; T_j = 150 °C	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C	-	-	2.25	V
I_{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	µA
		V_{DS} = 30 V; V_{GS} = 0 V; T_j = 150 °C	-	-	100	µA
I_{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 20 A; T_j = 25 °C; see Figure 12	-	4.75	5.7	mΩ
		V_{GS} = 4.5 V; I_D = 20 A; T_j = 150 °C; see Figure 12; see Figure 13	-	-	9.4	mΩ
		V_{GS} = 10 V; I_D = 20 A; T_j = 25 °C; see Figure 12	-	3.65	4.35	mΩ
		V_{GS} = 10 V; I_D = 20 A; T_j = 150 °C; see Figure 12; see Figure 13	-	-	7.25	mΩ
R_G	gate resistance	f = 1 MHz	-	1.9	3.8	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 20 A; V_{DS} = 15 V; V_{GS} = 10 V; see Figure 14; see Figure 15	-	23	-	nC
		I_D = 20 A; V_{DS} = 15 V; V_{GS} = 4.5 V; see Figure 14; see Figure 15	-	11	-	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V	-	20	-	nC
Q_{GS}	gate-source charge	I_D = 20 A; V_{DS} = 15 V; V_{GS} = 4.5 V; see Figure 14; see Figure 15	-	3.5	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	2.3	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	1.2	-	nC
Q_{GD}	gate-drain charge		-	3.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 20 A; V_{DS} = 15 V; see Figure 14; see Figure 15	-	2.66	-	V
C_{iss}	input capacitance	V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 16	-	1502	-	pF
C_{oss}	output capacitance		-	316	-	pF
C_{rss}	reverse transfer capacitance		-	106	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω; V_{GS} = 4.5 V; $R_{G(ext)}$ = 4.7 Ω	-	16	-	ns
t_r	rise time		-	19	-	ns
$t_{d(off)}$	turn-off delay time		-	24	-	ns
t_f	fall time		-	10	-	ns

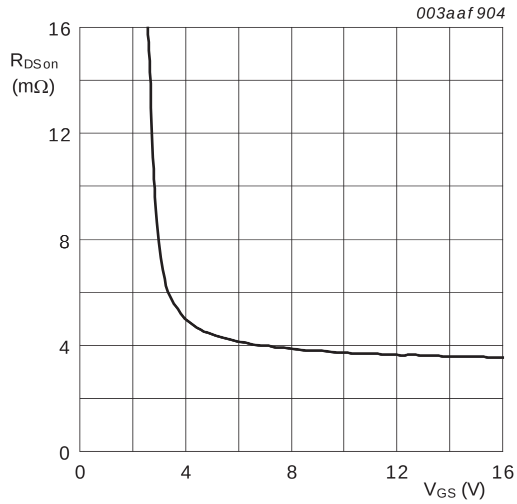
Table 7. Characteristics *…continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Q_{oss}	output charge	V_{GS} = 0 V; V_{DS} = 15 V; f = 1 MHz; T_j = 25 °C	-	8	-	nC
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 20 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 17	-	0.8	1.1	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 15 V	-	23	-	ns
Q_r	recovered charge		-	15	-	nC
t_a	reverse recovery rise time	V_{GS} = 0 V; I_S = 20 A; dI_S/dt = -100 A/µs; V_{DS} = 15 V; see Figure 18	-	13.5	-	ns
t_b	reverse recovery fall time		-	9.5	-	ns



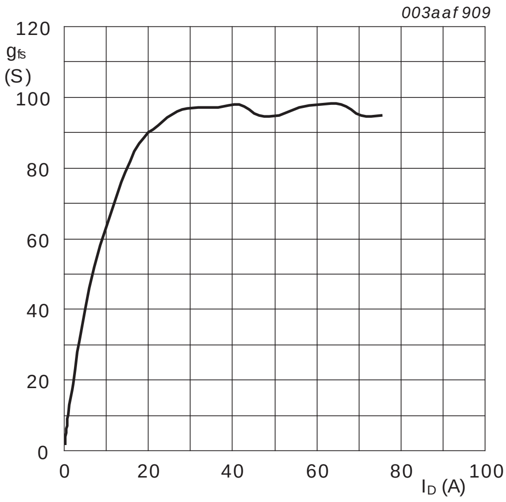
$T_j = 25°C$

Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



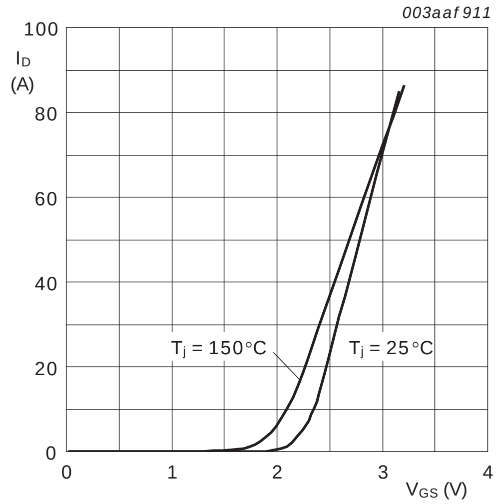
$T_j = 25°C;\ I_D = 20A$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



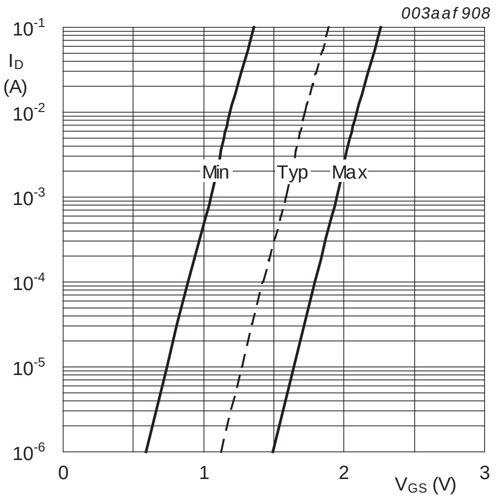
$T_j = 25°C;\ V_{DS} = 10V$

Fig 8. Forward transconductance as a function of drain current; typical values



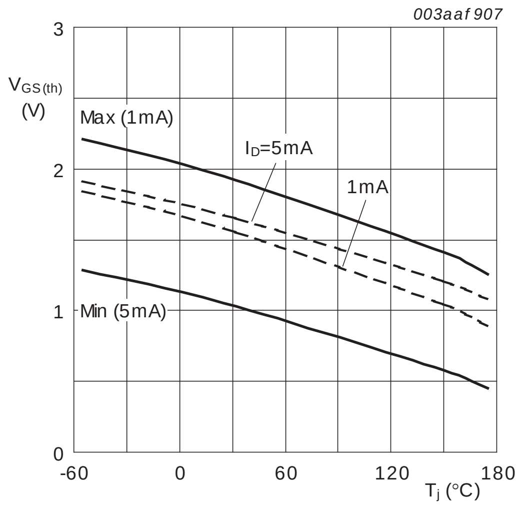
$V_{DS} = 10V$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



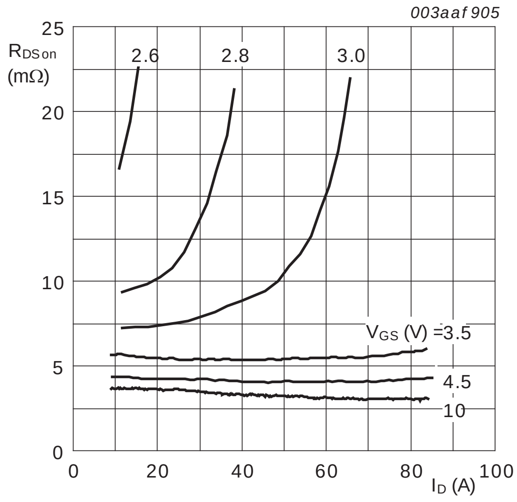
$T_j = 25°C;\ V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



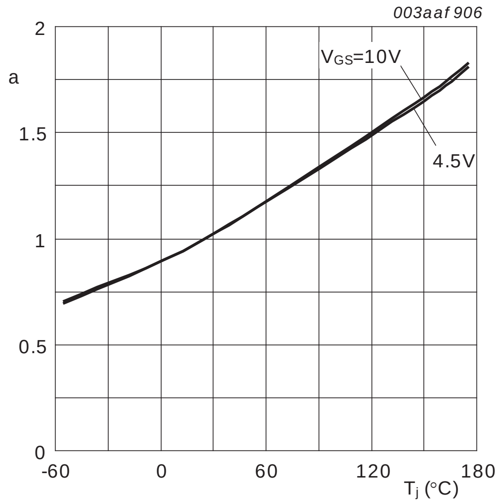
$V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature



$T_j = 25°C$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

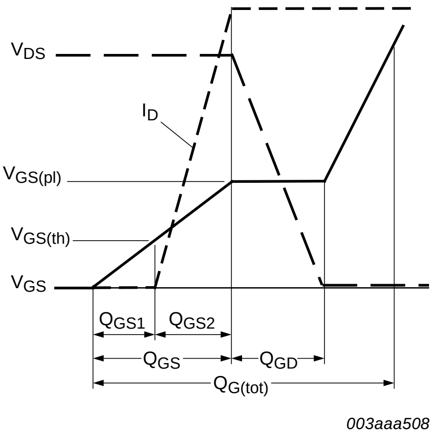
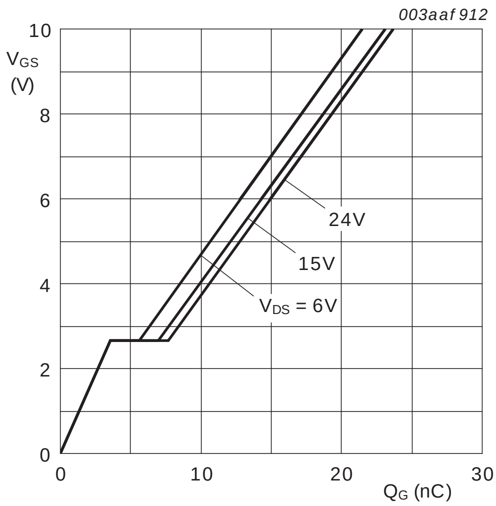
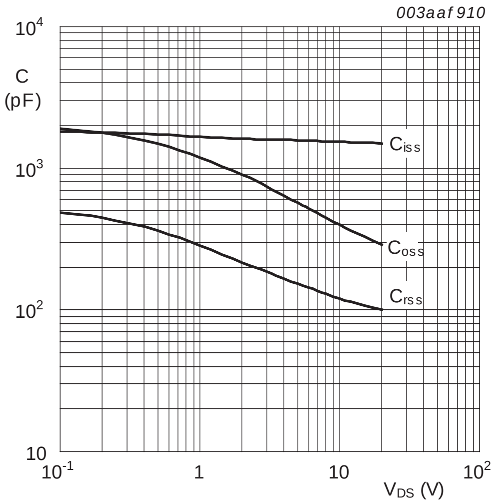


Fig 14. Gate charge waveform definitions



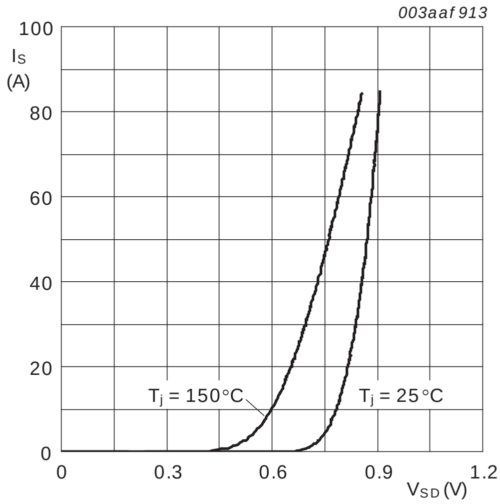
$T_j = 25°C;\ I_D = 20A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V;\ f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0V$

Fig 17. Source current as a function of source-drain voltage; typical values

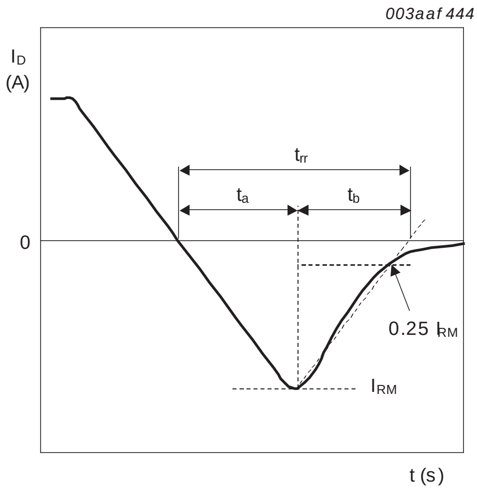
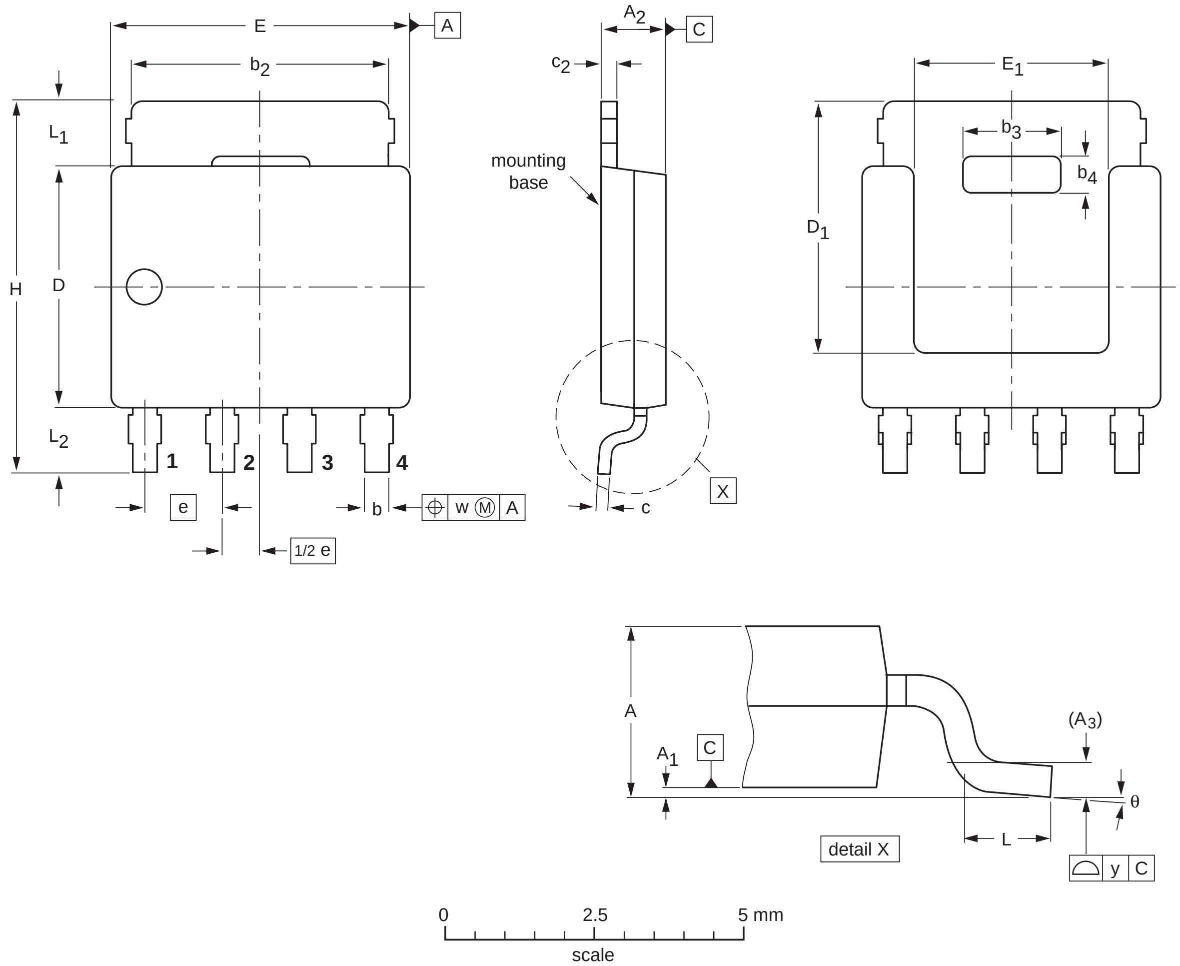


Fig 18. Reverse recovery timing definition

8. Package outline

Plastic single-ended surface-mounted package (LFPAK; Power-SO8); 4 leads **SOT669**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	A_2	A_3	b	b_2	b_3	b_4	c	c_2	D(1)	D_1(1) max	E(1)	E_1(1)	e	H	L	L_1	L_2	w	y	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT669		MO-235				~~06-03-16~~ 11-03-25

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R1-30YLC v.2	20110927	Product data sheet	-	PSMN4R1-30YLC v.1
Modifications:	• Various changes to content.			
PSMN4R1-30YLC v.1	20110502	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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12. Contents

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